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In one embodiment, select transistor 12 has an amorphous poly-silicon ("poly") gate 44s (formed as further explained below) and separated from a channel region 70 between drain region 40 and source region 60 by an oxide layer 50 which may be, for example, 168 Å thick. Select transistor 12's poly gate 44s is covered by a thin tungsten silicide layer 58s.

Please replace the paragraph beginning on page 5, line 11 with the following replacement paragraph:

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Oxide layer 50 may be thermally grown using a dry oxidation process at about 1050° C to a thickness of about 148 Å. A photoresist mask is then used to pattern for an etching step that exposes the substrate outside of the select transistors (e.g., select transistor 12). Then, a film of about 87 Å of oxide is formed as tunnel oxide 52 using a dry thermal oxidation process at about 1050° C. Due to the slower growth rate on oxide layer 50, oxide layer 50 only increases about 20 Å to a thickness of about 168 Å.

Please replace the paragraph beginning on page 6, line 15 with the following replacement paragraph:

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A retrograde distribution of dopant is then introduced by ion implantation into the channel regions 72, 74 and 76, while channel region 70 under select transistor 12 is masked by photoresist. The retrograde distribution of dopant is accomplished by implanting an n-type dopant (e.g., arsenic) at a tilt implant angle of, for example, 45° to vertical. Other tilt angles may also be suitable. The implantation can be made with a "batch-type" machine or with a single-wafer machine. In a batch-type machine, the wafer is rotated during the tilt implantation process. In a single-wafer machine, the implantation is done with a zero degree

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twist and a 180 degree twist (i.e., a tilt implantation through one side of source/drain regions 60, 62, and 64, followed by a like tilt angle implantation deposition through the source/drain regions 62, 64 and 66). Implantation energies between 80 and 110 KeV are suitable, forming resulting dopant concentrations of about 2×10^{-12} to 8×10^{-13} atoms per cm^2 .

Exhibit B is a marked-up version of the replacement paragraphs indicating the amendments.

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